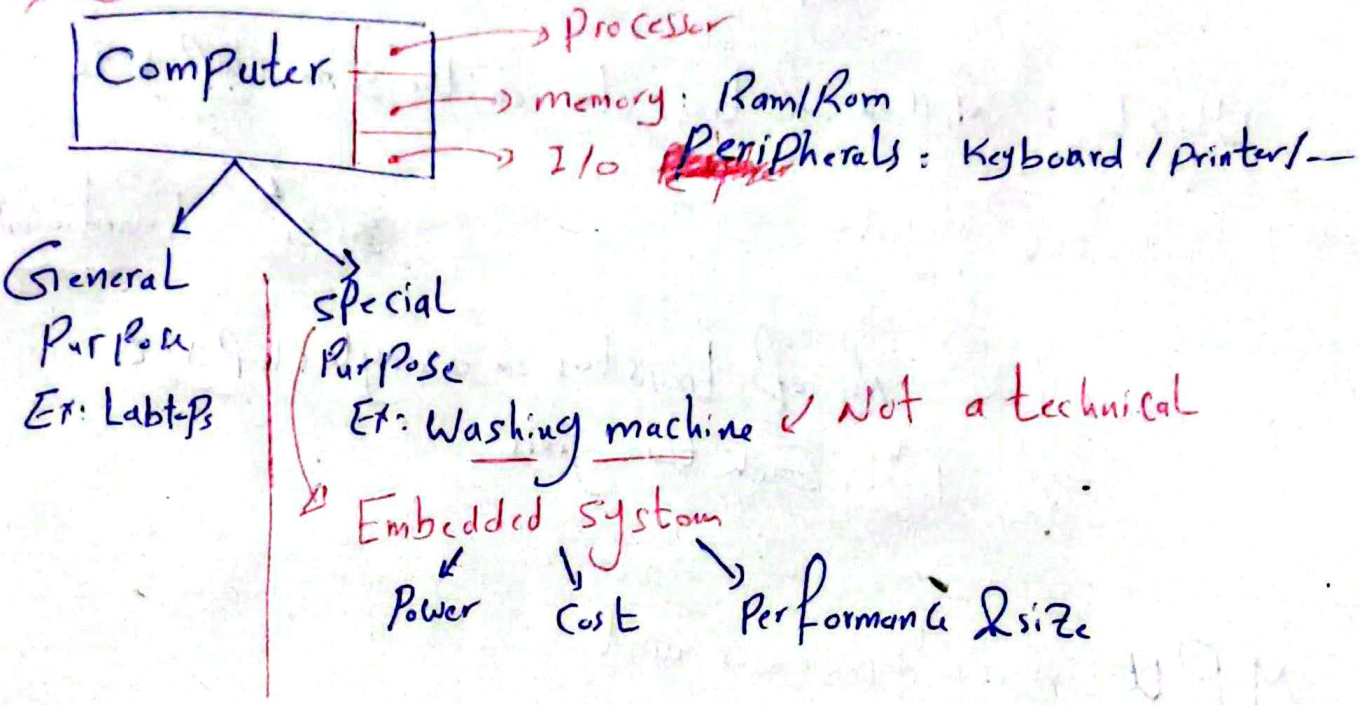
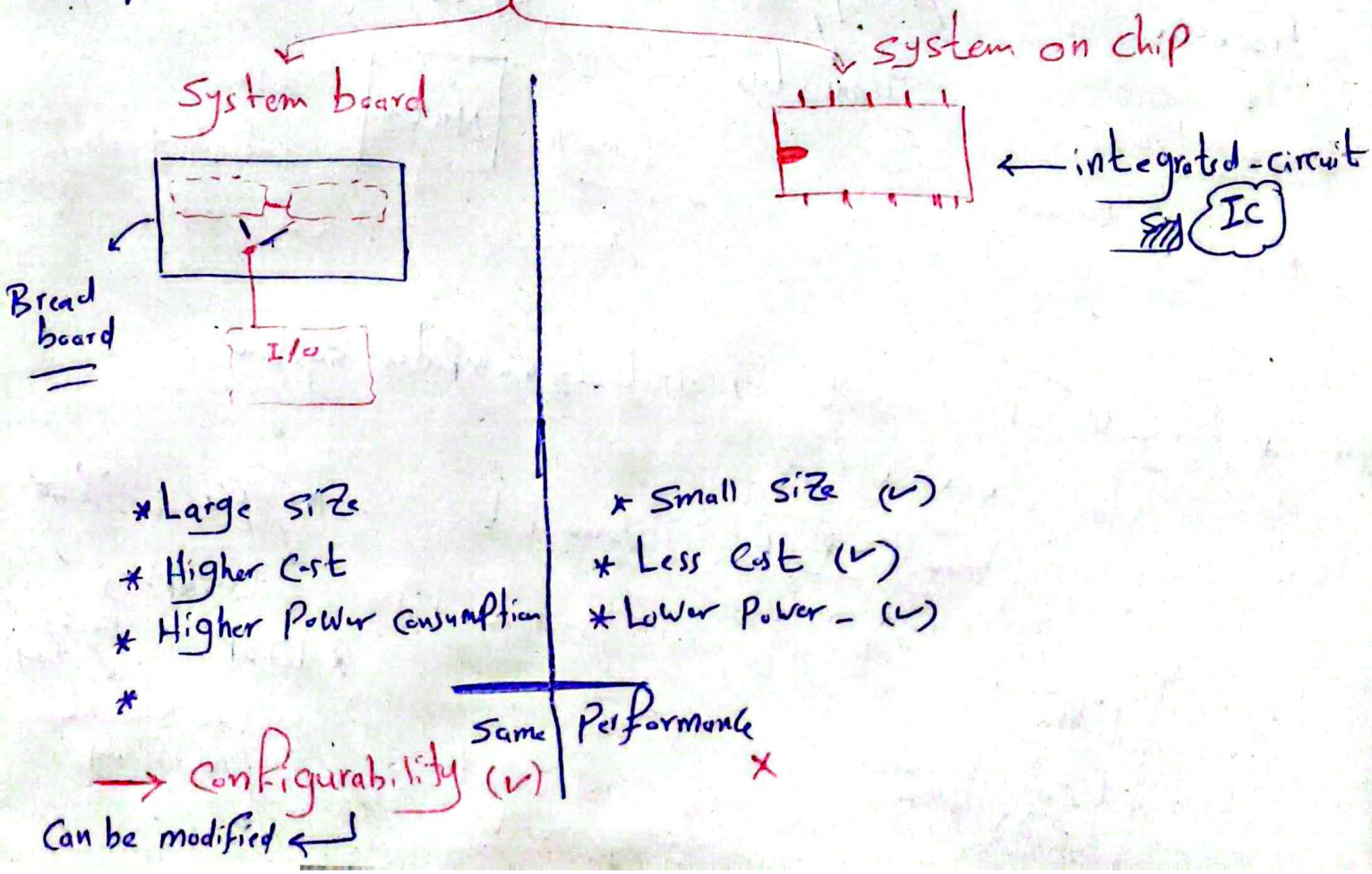
Embedded systems



How To make Es



IC : integrated_circuit → single circuit do a specific task according to its connection

Ex: Timer 555
op-amp

ULSI : Million of transistors on the same chip-size → size / functionality

ULSI → very large scale integration

* **Moore's Law** : No of transistors on a single chip-size doubles each two years

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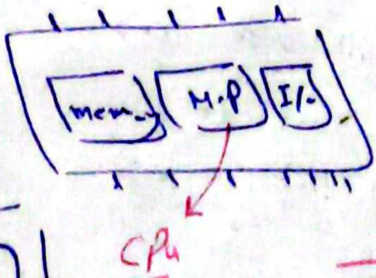
MPU : micro processor unit

- Processor → Vacuum tubes → Bit: 0 : Vacuum, 1 : charged
- Microprocessor → Transistors
- CPU → Central Processing unit

Master → Primary
GPU → secondary

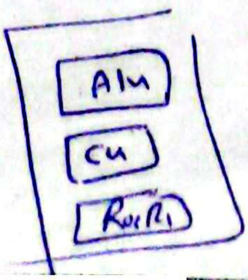
MP يكون ، (الأساسي في الشغل)

* **MCU : micro controller unit** → computer system



Ardunio kit + sensors & actuators

ECU
Electrical Control units

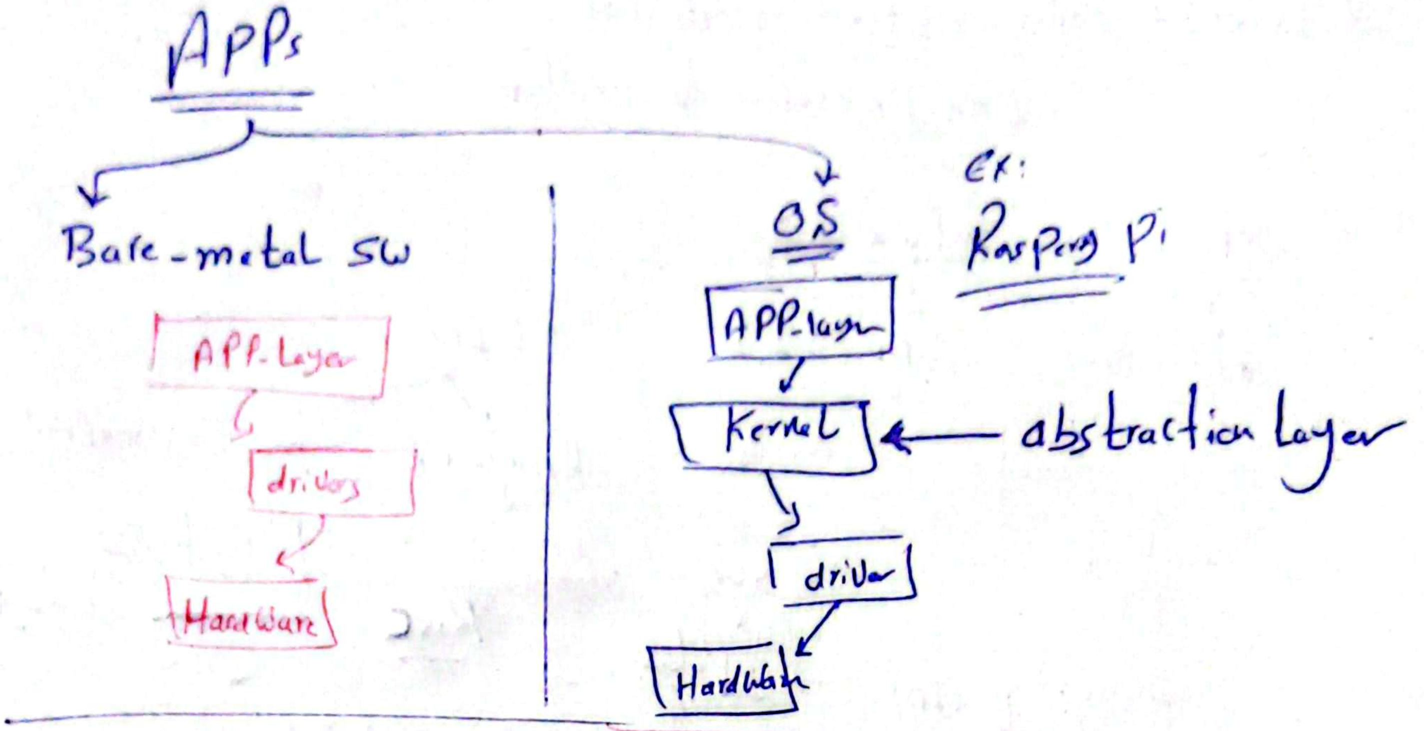


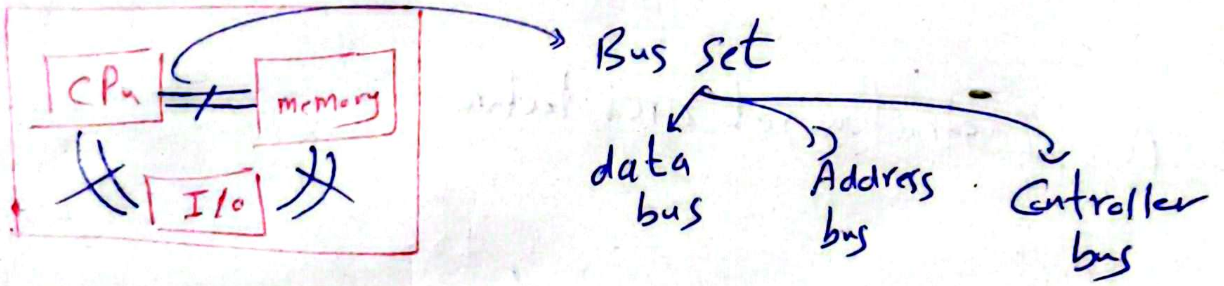
* GPU كارت الشاشة → Graphics

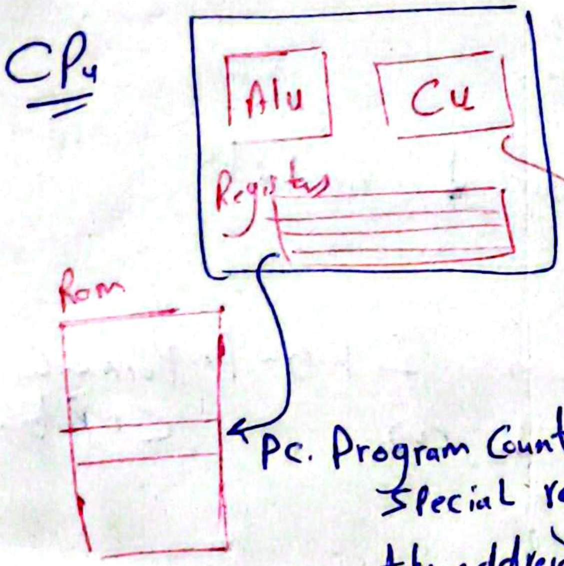
* DSP → Digital signal Processing

voice / temp.

APPs

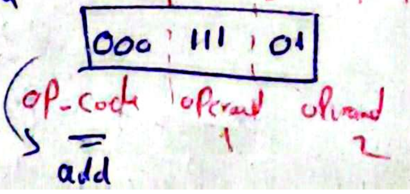






Instruction life cycle:
(Fetch - decode - execute)

- Fetch instruction from Rom to a Register (IR) instruction register
- Decode instruction by instruction Decoder (ID) < set: op-code dict, format Ex: 8-bit form
- Execute by Alu → General-Register



PC. Program Counter: special register keeps the address of next instruction ← اللي عليها الدور في التنفيذ

* Assembly codes, instructions differ one processor to another

(+ -) mpu 1 — add ...

mpu 2 (+ - * ÷) — ADD 111

(ID)

Instruction needs

HW → Instruction decoder (ID)

SW → Compiler

Hard wired → Logic gates → RISC

memory mapped → set → search in memory → CISC

* * 5 ⇌ + + + + +

ISA : Instruction set architecture

RISC → Reduced

inst. ↓

* software ↑

CISC → Complex

* software ↓ , need n't

RISC

Size ↑ Hardware

Alu ↓

cost HW ↓ SW ↑

Performance ↑

Power Alu ↓ ID ↑

CISC → High Performance Computer

Size ↓ (V)

Alu ↑

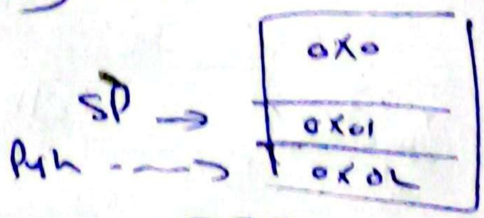
~ SW ↓ HW ↑

~ Performance ↑ (Search)

~ Alu ↑ ID ↓

Registers

- General Purpose
  - ↓ data store (Temporary)
  - * register int x;
    - ↙ Stored in CPU Not Ram
  - &x → Error
    - Can't access address
    - ↙ Access by name: $r_0, r_1, r_2, \ldots$
- Special Function
  1. PC: store address of next instruction
     - ↓ Program Counter
  2. SP → Stack Pointer
     - Memory لـ بيشاور عليها



  3. Accumulator → (Old)
  4. IR → instruction register
     - store instruction after fetching
  5. PSW → Process status Word
     - { 0 → +ve, 1 → -ve } ← sign flag, overflow, Zero
     - Flags → بيغيروا آخر Ins. دخلت عالـ Alu

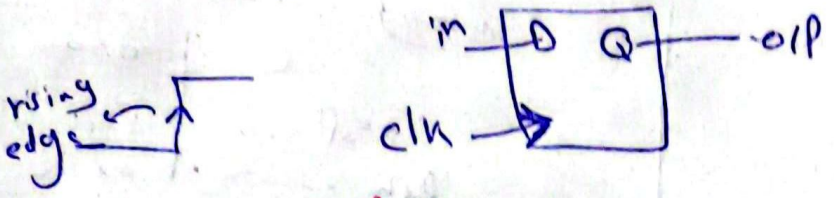
8 bit microprocessor
↳ register: 8 bit size

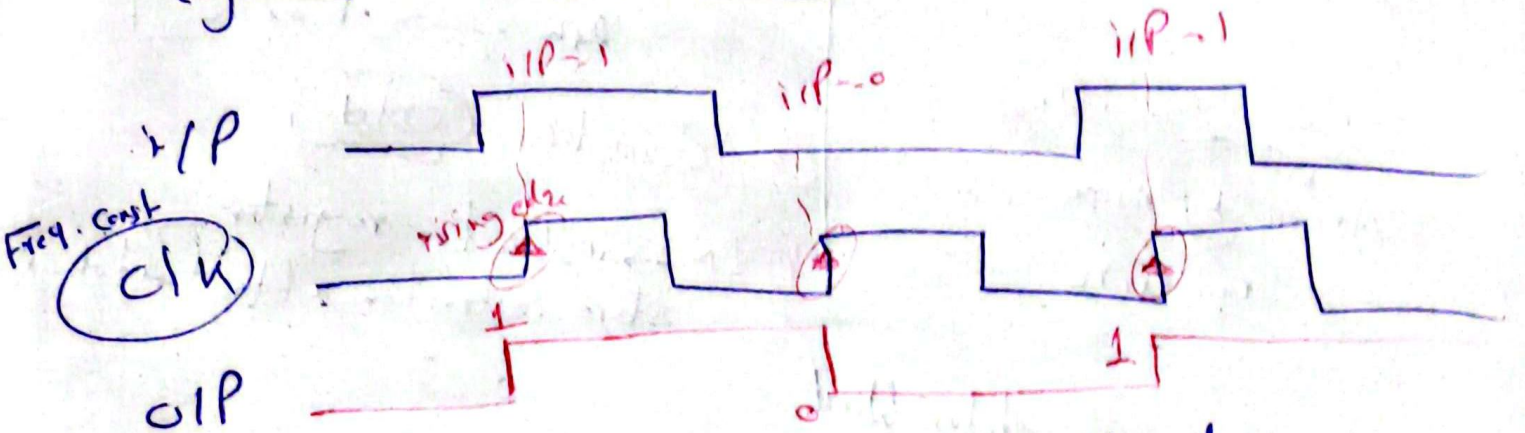
Memory :- Locations → Ex: Location is 8-bit size.

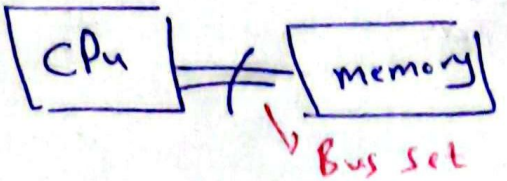
Access time (R / W)

Faster Slower

- Basic memory elements: Flip Flop - bit







Memory characteristics

① Capacity size → Address lines

② speed Access time

③ organize 4K x 4 = (16K)

data Address Control → R → 0, W → 1

No. data lines (Bits) → No. of memory bit in Location

2^n Locations → No. of address Lines (Bits)

data lines → Word size

Address lines → No. of accessable Locations

Memory types :-

memory

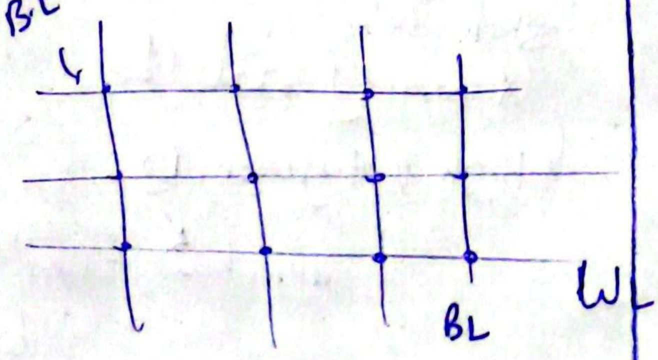
- Volatile — RAM
- Non Volatile — ROM
- Hybrid

① Volatile : RAM Random Access Memory
RWM Random Working memory

SRAM : Based on transistor
↳ Static

bit → flib flob
↓
min: 6 Transistors
2 Mosfets & 2 inverters

Bit



* No need for refreshment circuit
↳ Faster
* High Cost Per bit

DRam
↳ Dynamic : Capacitor & simple Mosfet
- discharged — Bit 0
- charged — Bit 1

المشكلة : المكثف بيفرغ شحنته بعد فترة

↳ Refreshment Circuit — DRam Controller
↓
- Higher Piority than CPu on Memory
- → Access time inc. & speed dec.

الحل : SRam

Dram Advantages

* Simple hardware
* low Cost Per bit
* high density
* Low Power Consumption (Mosfet) → sRam is lower due to refreshment Circuit of Dram

Ex → SRAM → Constraints (Cash)

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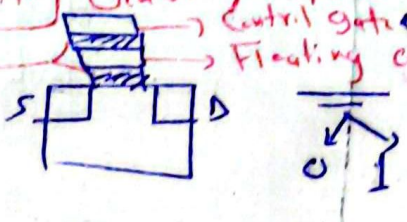
12 Non-Volatile Rom Read only memory (MP)

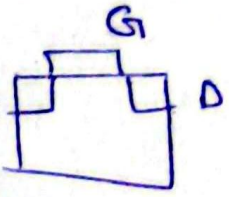
PC read From (Program memory)

Rom Saves Program instr. slower than Ram

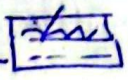
Based on Floating Gate Mosfet



Mosfet



High Voltage by Flasher



Programming state (0)

X erasing state (1)

↳ High Voltage on D ← attraction

charge (F.G)

0 → Programming state

1 → erasing state

Types of Rom

① Mask Programmable Rom
OTP → one time Program
* Bios chip
* Toys

② PRom
Programmable Rom
OTP → by (User)

Fuse
0 ↗ 1

③ EPRom → Erasable Programmable Rom
(UV) → لازم تمسح بالأشعة

Noise & Radiation sensitive → data Corruption

Hybrid → Rom + Rom
Read & write non Volatile

E^2PRom
- Electrical Erasable
- Endurance → 100,000 write & erase cycles
- Byte Access
- high cost Per bit

EEProm
- internal → Peripheral
- External → Communication Protocol

Flash
- Faster than E^2PRom
- Block Access → sector by sector
- Endurance 10,000
- Low Cost Per bit

nuRam
SRAM + Battery / E^2PRom + battery
- Faster than Rom
- High Cost Per bit

sRam + battery → Backup
sRam + E^2PRom + battery → move data